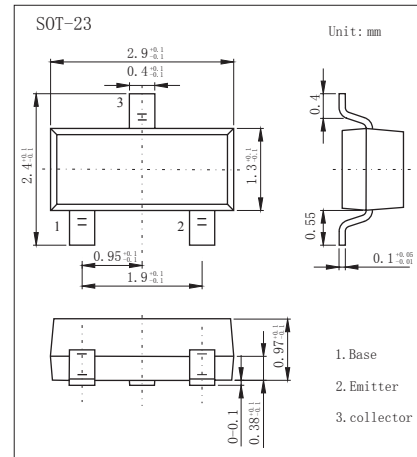


PNP Transistors

S9015

■ Features

- Complementary to KST9014



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	-50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-45	V
Emitter-Base Voltage	V <sub>EB0</sub>	-5	V
Collector Current -Continuous	I <sub>C</sub>	-0.1	A
Collector Power Dissipation	P <sub>C</sub>	0.2	W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to 150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>CB0</sub>	I <sub>C</sub> =-100uA, I <sub>E</sub> =0	-50			V
Collector-emitter breakdown voltage	V <sub>CEO</sub>	I <sub>C</sub> =-1mA, I <sub>B</sub> =0	-45			V
Emitter-base Breakdown voltage	V <sub>EB0</sub>	I <sub>E</sub> =-100 uA, I <sub>C</sub> =0	-5			V
Collector cutoff current	I <sub>CB0</sub>	V <sub>CB</sub> =-50V, I <sub>E</sub> =0			-0.1	μ A
Emitter cutoff current	I <sub>EB0</sub>	V <sub>EB</sub> =-5V, I <sub>C</sub> =0			-0.1	μ A
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-1mA	200		1000	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-100mA, I <sub>B</sub> =-10mA			-0.3	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-100mA, I <sub>B</sub> =-10mA			-1	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-10mA, f=30MHZ	150			MHz

■ hFE Classification

Type	S9015-L	S9015-H
Range	200-450	450-1000
Marking	M6	



炬芯微  
XUANXINWEI

SMD Type

Transistors

S9015

Typical Characteristics

